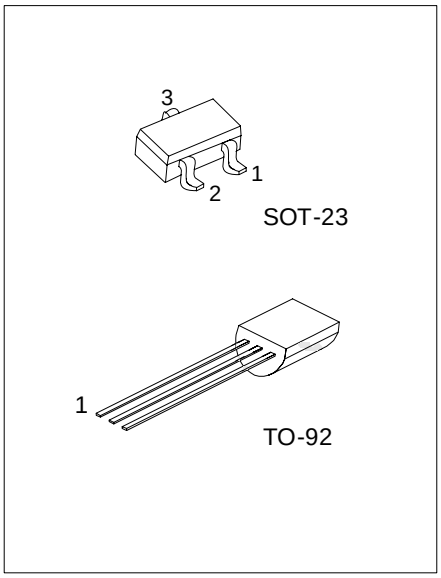
8550S

PNP SILICON TRANSISTOR

LOW VOLTAGE HIGH CURRENT SMALL SIGNAL PNP TRANSISTOR



*Pb-free plating product number: 8550SL

■ FEATURES

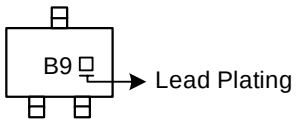
*Collector current up to 700mA
*Collector-Emitter voltage up to 20 V
*Complimentary to 8550S

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
8550S-x-AE3-R	8550SL-x-AE3-R	SOT-23	E	B	C	Tape Reel
8550S-x-T92-B	8550SL-x-T92-B	TO-92	E	C	B	Tape Box
8550S-x-T92-K	8550SL-x-T92-K	TO-92	E	C	B	Bulk

8550SL-x-AE3-R (1)Packing Type (2)Package Type (3)Rank (4)Lead Plating	(1) B: Tape Box, K: Bulk, R: Tape Reel (2) AE3: SOT-23, T92: TO-92 (3) x: refer to Classification of h_{FE2} (4) L: Lead Free Plating, Blank: Pb/Sn

■ MARKING (For SOT-23 Package)



■ ABSOLUTE MAXIMUM RATINGS (Ta = 25℃)

PARAMETER		SYMBOL	RATING	UNITS
Collector-Base Voltage		V_{CBO}	-30	V
Collector-Emitter Voltage		V_{CEO}	-20	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Dissipation(Ta=25℃)	SOT-23	P_C	350	mW
	TO-92		1	W
Collector Current		I_C	-700	mA
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25℃, unless otherwise specified)

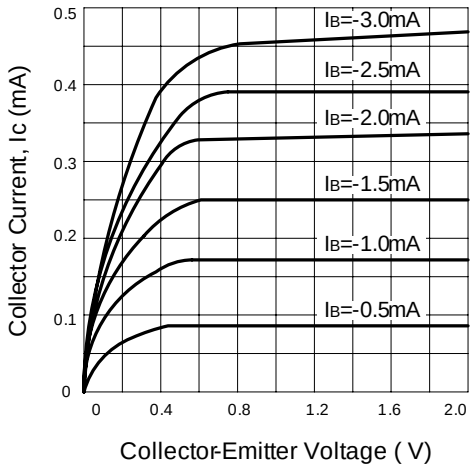
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	Ic=-100μA,I_E=0	-30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	Ic=-1mA,I_B=0	-20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=-100μA,Ic=0	-5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-30V,I_E=0			-1	uA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V,Ic=0			-100	nA
DC Current Gain	h_{FE1}	V_{CE}=-1V,Ic=-1mA	100			
	h_{FE2}	V_{CE}=-1V,Ic=-150 mA	120		400	
	h_{FE3}	V_{CE}=-1V,Ic=-500mA	40			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	Ic=-500mA,I_B=-50mA			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	Ic=-500mA,I_B=-50mA			-1.2	V
Base-Emitter Saturation Voltage	V_{BE}	V_{CE}=-1V,Ic=-10mA			-1.0	V
Current Gain Bandwidth Product	f_T	V_{CE}=-10V,Ic=-50mA	100			MHz
Output Capacitance	Cob	V_{CB}=-10V,I_E=0, f=1MHz		9.0		pF

■ CLASSIFICATION OF h_{FE2}

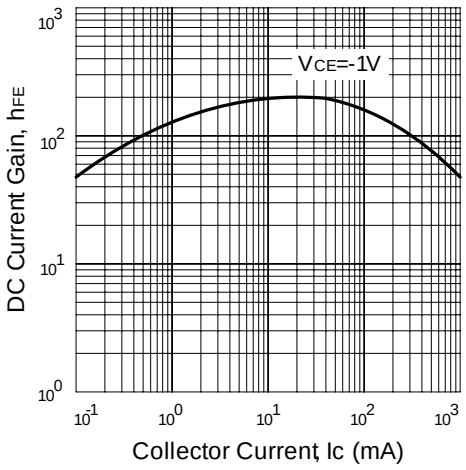
RANK	C	D	E
RANGE	120-200	160-300	280-400

■ TYPICAL CHARACTERISTICS

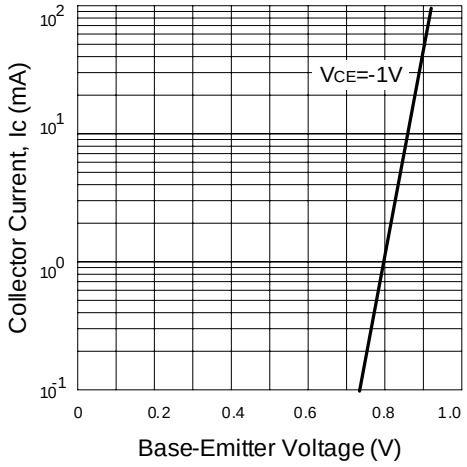
Static Characteristics



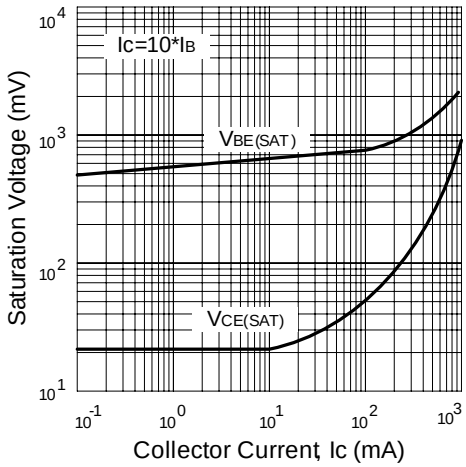
DC Current Gain



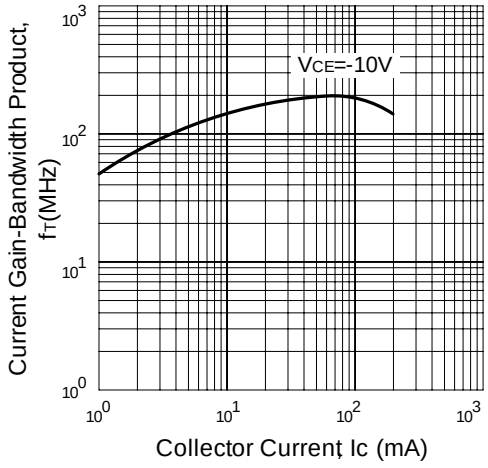
Base-Emitter on Voltage



Saturation Voltage



Current Gain-Bandwidth Product



Collector Output Capacitance